

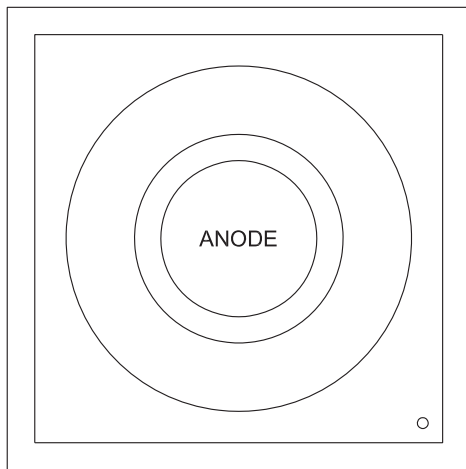
**PROCESS CPD66X**  
**Low Leakage Diode**  
Low Leakage Diode Chip



**PROCESS DETAILS**

Die Size	17.5 x 17.5 MILS
Die Thickness	5.9 MILS
Anode Bonding Pad Area	7.9 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

**GEOMETRY**



BACKSIDE CATHODE R0

**GROSS DIE PER 5 INCH WAFER**

54,848

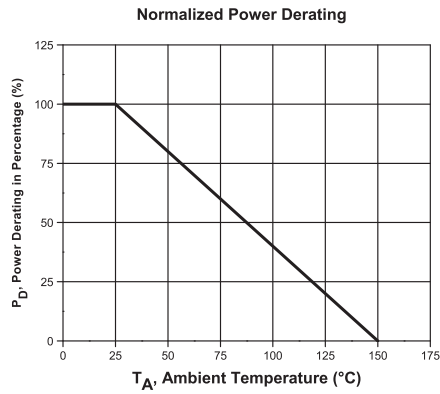
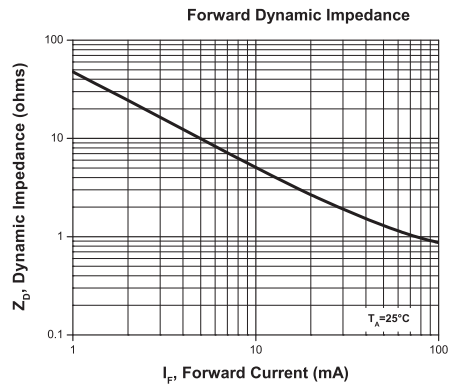
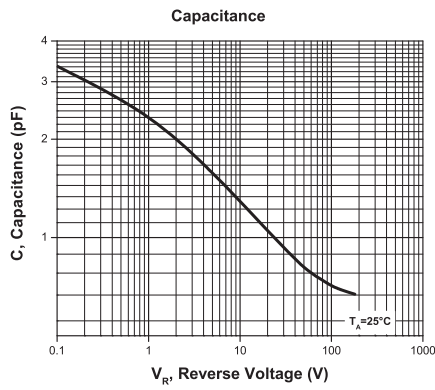
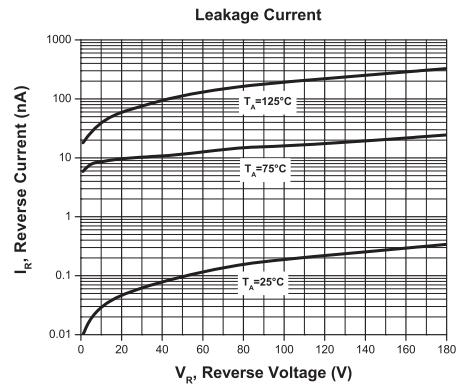
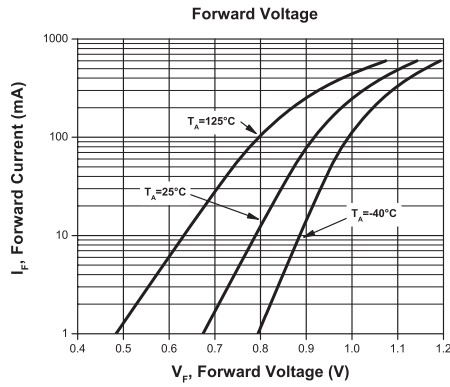
**PRINCIPAL DEVICE TYPES**

- CMOD3003
- CMLD3003DOG
- CMPD3003A
- CMPD3003C
- CMPD3003S

R1 (19-July 2010)

# PROCESS CPD66X

## Typical Electrical Characteristics



R1 (19-July 2010)